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				Application Number	
				Filing Date	
				First Named Inventor	
				Art Unit	
Examiner Name		Dingjun Wu, et al.			
Sheet	1	of	2	Attorney Docket Number	06469 USA

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
		US- 2001/0011526 A1	8/9/2001	K. Doering, et al.	
		US- 2001/0055852 A1	12/27/2001	T. S. Moise, et al.	
		US- 5,288,662	2/24/1994	A. Lagendijk, et al.	
		US- 5,298,075	3/29/1994	A. Lagendijk, et al.	
		US- 5,356,478	10/18/1994	C. Chen, et al.	
		US- 5,454,903	10/3/1995	F. C. Redeker, et al.	
		US- 5,756,400	5/26/1998	Y. Ye, et al.	
		US- 5,879,459	3/9/1999	P. N. Gadgil, et al.	
		US- 5,972,722	10/26/1999	M. R. Visokay, et al.	
		US- 6,174,377	1/16/2001	K. Doering, et al.	
		US- 6,211,035	4/3/2001	T. S. Moise, et al.	
		US- 6,238,582	5/29/2001	K. E. Williams, et al.	
		US- 6,387,185	5/14/2002	K. Doering, et al.	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
		EP 1 001 459 A2	5/17/2000	Europe		✓
		WO 00/40772	7/13/2000	World		✓
		WO 00/79019 A1	12/28/2000	World		✓
		WO 02/43114 A2	5/30/2002	World		✓
		WO 02/43115 A2	5/30/2002	World		✓

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		K. K. Shih, "Hafnium Dioxide Etch-Stop Layer for Phase-Shifting Masks," J. Vac. Sci. Technol. B 11(6), pp. 2130-2131(1993).	✓
		J. A. Britten, "Etch-Stop Characteristics of Sc <sub>2</sub> O <sub>3</sub> and HfO <sub>2</sub> Films for...", J. Vac. Sci. Technol. A 14(5), pp. 2973-2975 (1996).	✓
		J. Hong, "Comparison of Cl <sub>2</sub> and F <sub>2</sub> Based Chemistries for the...", J. Vac. Sci. Technol. A 17(4), pp. 1326-1330 (1999).	✓
		J. W. Lee, "Electron Cyclotron Resonance Plasma Etching of Oxides...", J. Vac. Sci. Technol. A 16(3), pp. 1944-1948.	✓
		W. G. M. van den Hoek, "The Etch Mechanism for Al <sub>2</sub> O <sub>3</sub> in Fluorine and Chlorine Based RF Dry Etch Plasma," Mat. Res. Soc. Symp. Proc., 68, pp. 71-78 (1986).	✓
		J. E. Spencer, et al., "Emission Spectroscopy of CC14 and BC13 Plasma During Aluminum Etching," Proceedings—Electrochemical Society, 82-7, pp. 103-107 (1982).	✓
		T. Kanninen, et al., "Growth of Dielectric HfO <sub>2</sub> /Ta <sub>2</sub> O <sub>5</sub> Thin Film Nanolaminate Capacitors by Atomic Layer Epitaxy," Proceedings—Electrochemical Society, 97-31, pp. 36-46 (1998).	✓
		H. B. Bell, et al., "Reactive Ion Etching of Aluminum/Silicon in BBr <sub>3</sub> /Cl <sub>2</sub> and BCl <sub>3</sub> /Cl <sub>2</sub> Mixtures," Journal of Electrochemical Society, 135(5), pp. 1184-91 (1988).	✓
		Y. S. Lee, et al., "Mass Spectrometric Characterization of BCl <sub>3</sub> /SF <sub>6</sub> Plasmas," Journal of Applied Physics, 88(8), pp. 4507-4509 (1980).	✓
		N. Heiman, et al., "High Rate Reactive Ion Etching of Al <sub>2</sub> O <sub>3</sub> and Si," J. Vac. Sci. Technol., 17(3), pp. 731-734 (1980).	✓
		K. Shibata, et al., "Manufacturing Method and its Equipment of Thin Film Magnetic Head," Japanese Patent Application JP2000251221A (2000).	✓
		J. Chen, et al., "Formation of Polycrystalline Silicon Germanium/HfO <sub>2</sub> Gate Stack Structure Using Inductively Coupled Plasma Etching," J. Vac. Sci. Technol. A 21(4), pp. 1210-1217 (2003).	✓

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